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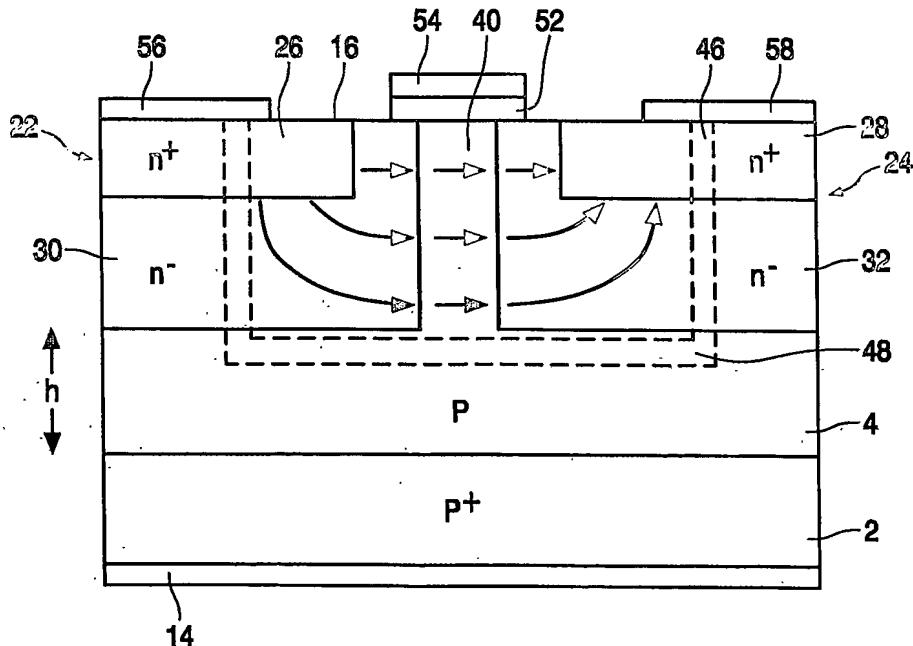
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[Continued on next page]

(54) Title: TRENCH MOS STRUCTURE



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(57) Abstract: A semiconductor device has a trench (42) adjacent to a cell (18). The cell includes source and drain contact regions (26,28), and a central body (40) of opposite conductivity type. The device is bidirectional and controls current in either direction with a relatively low on-resistance. Preferred embodiments include potential plates (60) that act together with source and drain drift regions (30,32) to create a RESURF effect.

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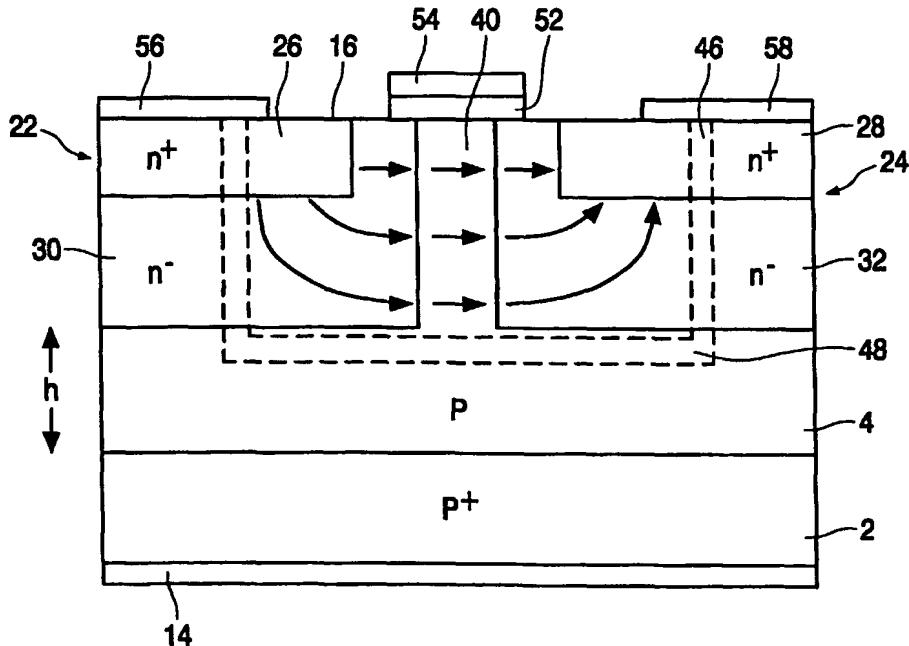
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